MECHANISMS OF CONDUCTIVITY IN AN *n*-ZrNiSn INTERMETALLIC SEMICONDUCTOR HEAVILY DOPED WITH Co. 2. ELECTRON STRUCTURE CALCULATIONS

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S u m m a r y

The electron structure of a ZrNiSn intermetallic semiconductor heavily doped with an acceptor impurity (by substituting Co atoms for Ni ones) has been calculated. The density of states at the Fermi level has been demonstrated to oscillate depending on the acceptor impurity concentration.